Poster Presentation

[AMDp2]Active-Matrix Devices

Thu. Nov 28, 2019 2:30 PM - 5:00 PM Main Hall (1F)

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[AMDp2-14L]E/E Inverter Using Four-Terminal Poly-Ge_xSn_{1-x} TFTs on Glass

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We demonstrated an E/E inverter using polycrystalline germanium-tin (poly-Ge_xSn_{1-x}) thin-film transistors (TFTs) fabricated via metal-induced crystallization (MIC) using Cu. The TFTs in the E/E inverter comprises a planar four-terminal (4T) structure, in which the TFTs were enabled to be normally-off by the control gate voltage (V_{CG}). The inverter performance was varied by changing V_{CG}.